

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1.-9. (Canceled)

10. (Currently Amended) A substrate for a liquid crystal panel ~~substrate~~ comprising:

a pixel region having reflecting electrodes formed on a semiconductor substrate and a switching element formed corresponding to each of the reflecting electrodes;
a periphery region arranged in a periphery of the pixel region, the periphery region having a laminate structure comprising a metal layer and an insulating layer formed above the substrate;

a scribed region ~~formed~~ arranged on an outer side of the periphery region, a step formed between the periphery region and the scribed region, the laminate structure having a sidewall at the step; and ~~of the pixel region; and~~

a passivation film covering the sidewall of the laminate structure and comprising ~~formed by a silicon nitride film, and formed on the scribed region of said semiconductor substrate.~~

11. (Currently Amended) A The substrate for the liquid crystal panel ~~substrate~~ according to claim 10, ~~said~~ the passivation film ~~having~~ has a laminate structure comprising a silicon oxide film and the silicon nitride film formed on the silicon oxide film.

12.-15 (Canceled)

16. (New) The substrate for the liquid crystal panel according to claim 11, further comprising a second passivation film formed on the reflecting electrodes and formed by a silicon oxide film, said silicon oxide film of the passivation film in the periphery region is same layer as the silicon oxide film of the second passivation film in the pixel region.

17. (New) A liquid crystal panel, comprising:
- a first substrate;
 - a second substrate opposed to the first substrate;
 - a liquid crystal there between;
 - a pixel region having reflecting electrodes formed on the first substrate and a switching element formed corresponding to each of the reflecting electrodes,
 - a periphery region arranged in the periphery of the pixel region, the periphery region having a laminate structure comprising a metal layer and an insulating layer formed above the first substrate;
 - a scribed region arranged on an outer side of the periphery region, a step formed between the periphery region and the scribed region, the laminate structure having a sidewall at the step; and
 - a passivation film covering the sidewall of the laminate structure and comprising a silicon nitride film.
18. (New) The liquid crystal panel according to claim 17, said passivation film has a laminate structure comprising a silicon oxide film and the silicon nitride film formed on the silicon oxide film.
19. (New) The liquid crystal panel according to claim 18, further comprising a second passivation film formed on the reflecting electrodes and comprising a silicon oxide film, said silicon oxide film of the passivation film in the periphery region is a same layer as the silicon oxide film of the second passivation film in the pixel region.
20. (New) A substrate for a liquid crystal panel, comprising:
- a pixel region having reflecting electrodes formed on a substrate and a switching element formed corresponding to each of the reflecting electrodes;

a periphery region arranged in the periphery of the pixel region, the periphery region having a laminate structure comprising a metal layer and an insulating layer formed above the substrate;

a first passivation film formed on the laminate structure, comprising a silicon oxide film and a silicon nitride film formed on the silicon oxide film; and

a second passivation film covering the reflecting electrodes, comprising a silicon oxide film as a same layer as the silicon oxide film of the first passivation film.

21. (New) The substrate for the liquid crystal panel according to claim 20, further comprising a light shielding layer formed by a metal between the reflecting electrodes and the switching elements, and an insulating interlayer formed between the reflecting electrodes and the light shielding layer, the insulating interlayer comprising a second silicon nitride.

22. (New) The substrate for the liquid crystal panel according to claim 21, the second passivation film formed by the silicon oxide film on the reflecting electrodes and the insulating interlayer formed by the silicon nitride film between the reflecting electrodes and the light shielding layer, form a laminate structure at space between the adjacent reflecting electrodes.

23. (New) A liquid crystal panel, comprising:

- a first substrate;
- a second substrate opposed to the first substrate;
- a liquid crystal there between;
- a pixel region having reflecting electrodes formed on the first substrate and a switching element formed corresponding to each of the reflecting electrodes;
- a periphery region arranged in the periphery of the pixel region, the periphery region having a laminate structure comprising a metal layer and an insulating layer formed above the first substrate;

a first passivation film formed on the laminate structure, comprising a silicon oxide film and a silicon nitride film formed on the silicon oxide film; and

a second passivation film covering the reflecting electrodes, comprising a silicon oxide film as a same layer as the silicon oxide film of the first passivation film.

24. (New) The liquid crystal panel according to claim 23, further comprising a light shielding layer formed by a metal between the reflecting electrodes and the switching elements, and an insulating interlayer formed between the reflecting electrodes and the light shielding layer, the insulating interlayer comprising a second silicon nitride.

25. (New) The liquid crystal panel according to claim 24, wherein the second passivation film formed by the silicon oxide film on the reflecting electrodes and the insulating interlayer formed by the silicon nitride film between the reflecting electrodes and the light shielding layer, form a laminate structure at a space between the adjacent reflecting electrodes.

26. (New) A substrate for a liquid crystal panel, comprising:

a pixel region having reflecting electrodes formed on a substrate and a switching element formed corresponding to each of the reflecting electrodes;

a light shielding layer formed by a metal between the reflecting electrodes and the switching elements;

an insulating interlayer formed between the reflecting electrodes and the light shielding layer, the insulating interlayer comprising a second silicon nitride; and

a passivation film covering the reflecting electrodes and a space between the adjacent reflecting electrodes, the passivation film comprising a silicon oxide film,

the passivation film formed by the silicon oxide film and the insulating interlayer formed by the silicon nitride film form a laminate structure at the space between the adjacent reflecting electrodes.